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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Re Patent Application of

MAI ET AL.

Atty. Ref.: 1035-650

Serial No. 10/589,390

Group: 2812

Filed: August 15, 2006

Examiner: Unknown

For: Thin Film Transistor, Method of Manufacturing Same,
Display Device, Method of Modifying An Oxide Film,
Method of Forming An Oxide Film, Semiconductor
Device, Method of Manufacturing Semiconductor
Device, and Apparatus For Manufacturing
Semiconductor Device

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Further to applicants' Information Disclosure Statement of April 10, 2007, applicants herewith submit a corrected Form PTO-1449 (i.e., the date of the first JP reference has been corrected and the Asuha et al reference title and Part number has been corrected).

Respectfully submitted,
NIXON & VANDERHYE P.C.

May 23, 2007

By: H. Warren Burnam, Jr.
H. Warren Burnam, Jr.
Reg. No. 29,366

HWB:lsh
901 North Glebe Road, 11th Floor
Arlington, VA 22203-1808
Telephone: (703) 816-4000
Facsimile: (703) 816-4100


**INFORMATION DISCLOSURE
CITATION**

ATTY. DOCKET NO.

SERIAL NO.

1035-650

10/589,390

APPLICANT

IMAI ET AL.

(Use several sheets if necessary)

FILING DATE

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	2003/0102793	6-2003	Komoda et al.			
	2005/0215070	9-2005	Kobayashi			
	6,221,788	4-2001	Kobayashi et al.			

FOREIGN PATENT DOCUMENTS

				TRANSLATION	
DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES NO
3-6826 A	1-1991	JP			Partial
52-78374	1-1977	JP			Partial
2002-57154 A	2-2002	JP			Partial
2002-64093 A	2-2002	JP			Partial

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	Sakamoto et al, "Formation of Anodic Reaction Film on n-type Si", Applied Physics, vol. 44, Issue No. 5, 1975, pp.497-506
	Tokuyama, "Comprehensive Treatise on Electronics Technology", Vol. 3, MOS Device, Kogyochosakai, 1976, pp.124-126
	Asusha et al, "Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density Formed by Chemical Oxidation of Si", Applied Physics Letters, Vol. 81, No. 18, 28 October 2002, pp. 3410-3412
	Kobayashi et al, "Nitric Acid Oxidation of Si to Form Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density", Journal of Applied Physics, Vol. 94, No. 11, American Institute of Physics, 2003, pp. 7328-7335
	Asuha et al, "Low Temperature Formation of SiO ₂ /Si Structure by Chemical Method and Spectroscopic Observation", Meeting Abstracts of the Physical Society of Japan, Vol. 58, Issue 2, Part 4, Meeting Abstracts, 2003, pp. 771-

Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)